查询"2SK390fccsnips Field Effect Transistor Silicon N-Channel MOS Type (π-MOSVI)

2SK3905

Switching Regulator Applications

Unit: mm

• Low drain-source ON resistance: RDS (ON) = 0.25Ω (typ.)

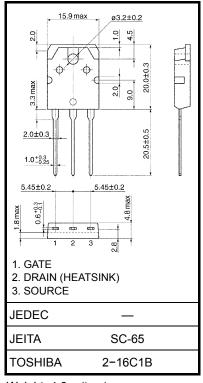
• High forward transfer admittance: $|Y_{fs}| = 8.2 \text{ S (typ.)}$

• Low leakage current: $I_{DSS} = 100 \mu A (max) (V_{DS} = 500 V)$

• Enhancement model: $V_{th} = 2.0 \sim 4.0 \text{ V}$ ($V_{DS} = 10 \text{ V}$, $I_{D} = 1 \text{ mA}$)

Absolute Maximum Ratings (Ta = 25°C)

Characteristic		Symbol	Rating	Unit		
Drain-source voltage			V_{DSS}	500	V	
Drain-gate voltage ($R_{GS} = 20 \text{ k}\Omega$)			V_{DGR}	500	V	
Gate-source voltage			V_{GSS}	±30	V	
Drain current	DC (Note	1)	ΙD	17	А	
	Pulse (Note	1)	I _{DP}	68	A	
Drain power dissipation (Tc = 25°C)			P _D	150	W	
Single pulse avalanche energy (Note 2)			E _{AS}	816	mJ	
Avalanche current			I _{AR}	17	Α	
Repetitive avalanche energy (Note 3)			E _{AR}	15	mJ	
Channel temperature			T _{ch}	150	°C	
Storage temperature range			T _{stg}	-55~150	°C	



Weight: 4.6 g (typ.)

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Thermal Characteristics

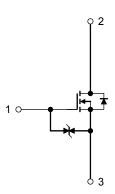
Characteristic	Symbol	Max	Unit	
Thermal resistance, channel to case	R _{th (ch-c)}	0.833	°C/W	
Thermal resistance, channel to ambient	R _{th (ch-a)}	50	°C/W	

Note 1: Ensure that the channel temperature does not exceed 150°C during use of the device.

Note 2: $V_{DD} = 90~V,~T_{ch} = 25^{\circ}C,~L = 4.8~mH,~R_{G} = 25~\Omega,~I_{AR} = 17~A$

Note 3: Repetitive rating: pulse width limited by max junction temperature

This transistor is an electrostatic-sensitive device. Handle with care.



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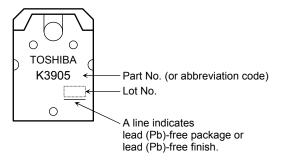
Energy (Ta = 25°C)

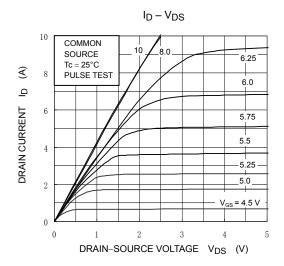
Char	acteristic	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage cur	eakage current I_{GSS} $V_{GS} = \pm 25 \text{ V}, V_{DS} = 0 \text{ V}$		_	_	±10	μА	
Drain-source breakdown voltage		V (BR) GSS	$I_G = \pm 10 \ \mu A, \ V_{DS} = 0 \ V$	±30	_	_	V
Drain cutoff current		I _{DSS}	V _{DS} = 500 V, V _{GS} = 0 V	_	_	100	μА
Drain-source brea	akdown voltage	V (BR) DSS	$I_D = 10$ mA, $V_{GS} = 0$ V	500	_	_	V
Gate threshold vo	oltage	V _{th}	V _{DS} = 10 V, I _D = 1 mA	2.0	_	4.0	V
Drain-source ON	resistance	R _{DS} (ON)	V _{GS} = 10 V, I _D = 8.5 A	_	0.25	0.31	Ω
Forward transfer	admittance	Y _{fS}	V _{DS} = 10 V, I _D = 8.5 A	2.3	8.2	_	S
Input capacitance	ut capacitance C _{iss}			_	3100	_	pF
Reverse transfer capacitance		C _{rss}	$V_{DS} = 25 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$	_	20	_	
Output capacitance		Coss		_	270	_	
Switching time	Rise time	t _r	$V_{GS} = 8.5 \text{ A} \\ V_{GS} = 24 \Omega$ $V_{DD} \approx 200 \text{ V}$ $V_{DD} \approx 200 \text{ V}$	_	70	_	ns
	Turn-on time	t _{on}		_	130	_	
	Fall time	t _f			70		
	Turn-off time	t _{off}		_	280	_	
Total gate charge (gate-source plus gate-drain)		Qg	$V_{DD} \simeq 400 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 17 \text{ A}$	_	62	_	
Gate-source charge		Q _{gs}		_	40	_	nC
Gate-drain ("Miller") charge		Q _{gd}		_	22	_	

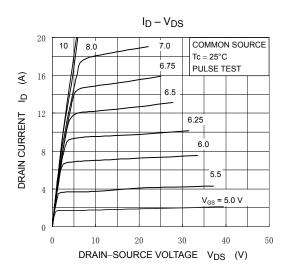
Source-Drain Ratings and Characteristics (Ta = 25°C)

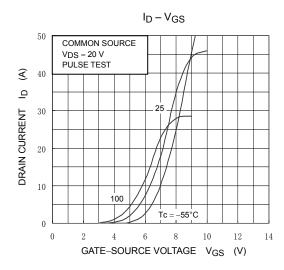
Characteristic	Symbol	Test Condition	Min	Тур.	Max	Unit
Continuous drain reverse current (Note 1)	I_{DR}	_	_	_	17	Α
Pulse drain reverse current (Note 1)	I _{DRP}	_	_	_	68	Α
Forward voltage (diode)	V _{DSF}	I _{DR} = 17 A, V _{GS} = 0 V	_	_	-1.7	V
Reverse recovery time	t _{rr}	I _{DR} = 17 A, V _{GS} = 0 V,	_	1300	_	μS
Reverse recovery charge	Q _{rr}	dI _{DR} /dt = 100 A/μs	_	18	_	μС

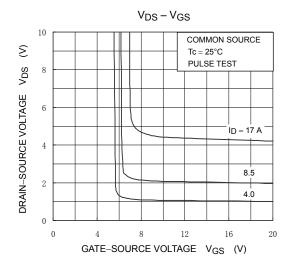
Marking

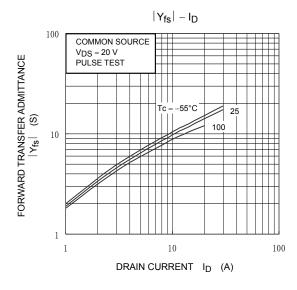


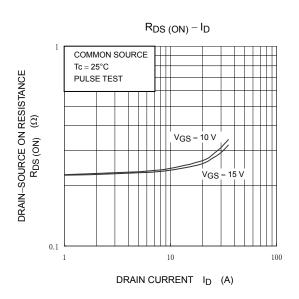


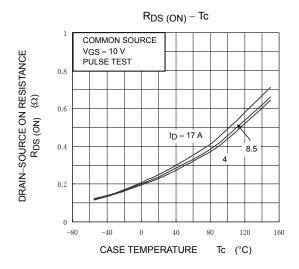


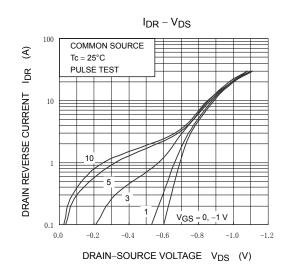


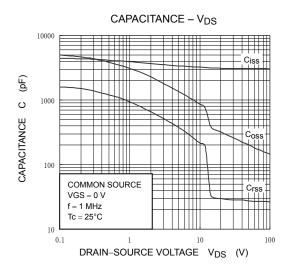


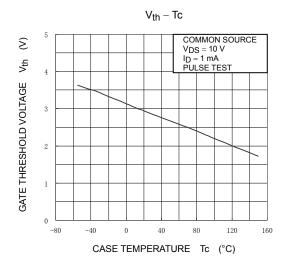


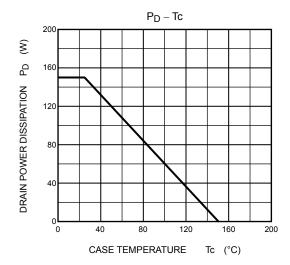


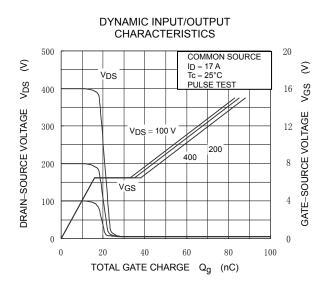


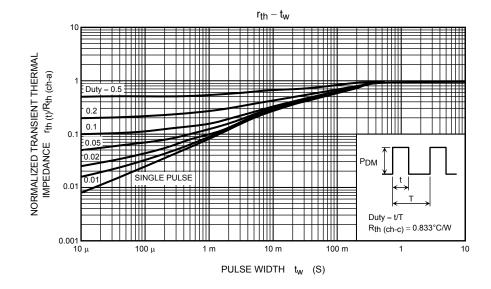


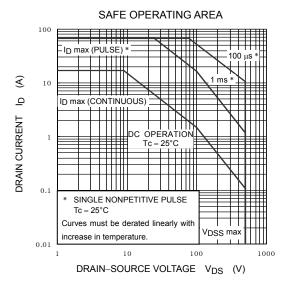


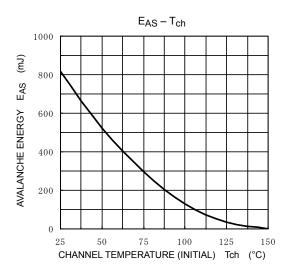


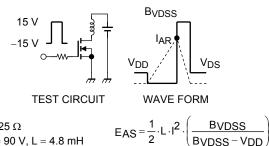












$$R_G = 25~\Omega$$

$$V_{DD} = 90~V,~L = 4.8~mH$$

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$$EAS = \frac{1}{2} \cdot L \cdot I^2 \cdot \left(\frac{BVDSS}{BVDSS - VDD} \right)$$

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